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Amend w/ Hach
SDavis
2/3/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: SHIMOYAMA, et al.

Serial No.: 09/785,428

Group Art Unit: 2814

Filed: February 20, 2001

Examiner: D. Wille

P.T.O. Confirmation No.: 1962

For: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

January 27, 2003

Sir:

In response to the Office Action dated July 25, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Please replace the paragraph beginning at page 10, line 5, with the following rewritten paragraph:

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B1
Thereafter, using the etching preventive film as mask and HC1 as etching gas, in-site gas etching of the semiconductor substrate or the epitaxial layer is performed, and a V-groove with sharp edge is formed. Using HC1 as the etching gas, the side of the V-groove is turned to a (111) B face

6. Besides HC1, a gas having at least one type of halogen element such as hydrogen bromide, arsenic trichloride, phosphorus trichloride, chlorine, etc. may be used as the etching gas, and it is